

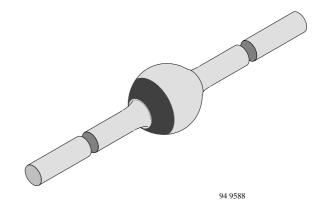
Very Fast Soft-Recovery Avalanche Rectifier

Features

- Glass passivated
- Hermetically sealed package
- Very low switching losses
- Low reverse current
- High reverse voltage

Applications

Switched mode power supplies High–frequency inverter circuits



Absolute Maximum Ratings

 $T_j = 25^{\circ}C$

Parameter	Test Conditions	Туре	Symbol	Value	Unit
Repetitive peak reverse voltage		BYM36A	V _{RRM}	200	V
		BYM36B	V _{RRM}	400	V
		BYM36C	V _{RRM}	600	V
		BYM36D	V _{RRM}	800	V
		BYM36E	V _{RRM}	1000	V
Reverse voltage		BYM36A	V_{R}	200	V
		BYM36B	V_{R}	400	V
		BYM36C	V_R	600	V
		BYM36D	V_{R}	800	V
		BYM36E	V_{R}	1000	V
Peak forward surge current	t _p =10ms, half sinewave		I _{FSM}	65	A
Average forward current		BYM36A	I _{FAV}	3	A
		BYM36B	I _{FAV}	3	A
		BYM36C	I _{FAV}	3	A
		BYM36D	I _{FAV}	2.9	A
		BYM36E	I _{FAV}	2.9	A
Non repetitive reverse avalanche energy	I _{(BR)R} =400mA, inductive load		E _R	10	mJ
Junction temperature			T_j	175	°C
Storage temperature range			T _{stg}	−55+175	°C



Maximum Thermal Resistance

 $T_j = 25\,^{\circ}C$

Parameter	Test Conditions	Symbol	Value	Unit
function ambient l=10mm, T _L =constant		R_{thJA}	25	K/W

Characteristics

 $T_j = 25^{\circ}C$

Parameter	Test Conditions	Type	Symbol	Min	Тур	Max	Unit
Forward voltage	I _F =3A	BYM36A	V_{F}			1.6	V
		BYM36B	V_{F}			1.6	V
		BYM36C	V _F			1.6	V
		BYM36D	V _F			1.78	V
		BYM36E	V_{F}			1.78	V
	I _F =3A, T _j =175 °C	BYM36A	V_{F}			1.22	V
		BYM36B	V_{F}			1.22	V
		BYM36C	V_{F}			1.22	V
		BYM36D	V_{F}			1.28	V
		BYM36E	V_{F}			1.28	V
Reverse current	$V_R = V_{RRM}$		I_R			5	μA
	$V_R = V_{RRM}, T_j = 150$ °C		I_R			100	μΑ
Reverse breakdown voltage	$I_R=100\mu A$	BYM36A	$V_{(BR)R}$	300			V
		BYM36B	$V_{(BR)R}$	500			V
		BYM36C	$V_{(BR)R}$	700			V
		BYM36D	$V_{(BR)R}$	900			V
		BYM36E	$V_{(BR)R}$	1100			V
Reverse recovery time	I _F =0.5A, I _R =1A, i _R =0.25A	BYM36A	t _{rr}			100	ns
		BYM36B	t _{rr}			100	ns
		BYM36C	t _{rr}			100	ns
		BYM36D	t _{rr}			150	ns
		ВҮМ36Е	t _{rr}			150	ns
Switching behaviour	I _F =2A, I _{RM} =1A, V _R =400V, Fig. 1		I_{SLP}			-200	mA



Typical Characteristics $(T_j = 25^{\circ}C \text{ unless otherwise specified})$

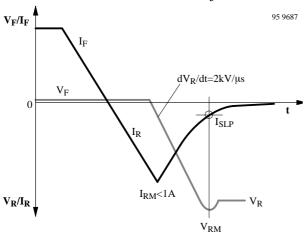


Figure 1. I_{SLP}-Definition

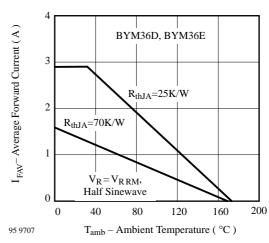


Figure 4. Average Forward Current vs. Ambient Temperature

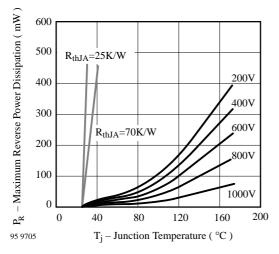


Figure 2. .Maximum Reverse Power Dissipation vs. Junction Temperature

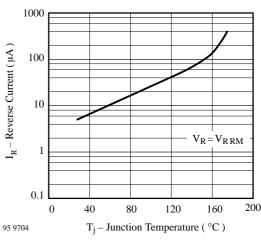


Figure 5. Reverse Current vs. Junction Temperature

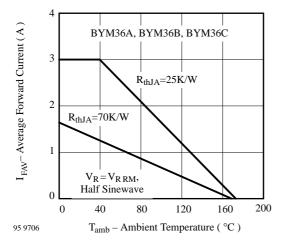


Figure 3. Average Forward Current vs. Ambient Temperature

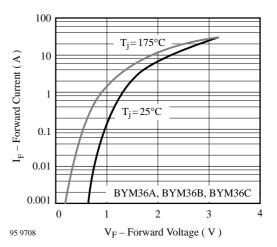


Figure 6. Forward Current vs. Forward Voltage

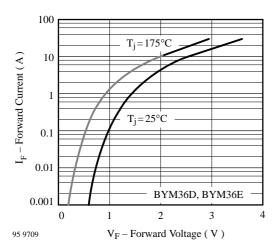
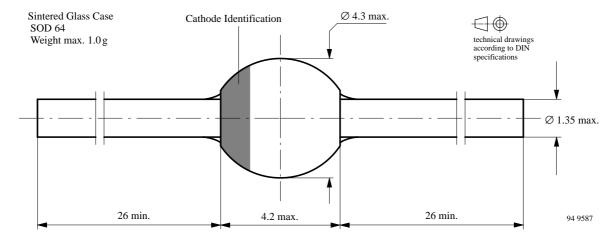


Figure 7. Forward Current vs. Forward Voltage

Dimensions in mm





Ozone Depleting Substances Policy Statement

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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